

FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Voltage Drop
- Isolated Base
- Dual Diodes Can Be Paralleled for 1800A Rating
- MMC Baseplate With AlN Substrates

APPLICATIONS

- Brake Chopper Diode
- Boost and Buck Converters
- Free-wheel Circuits
- Motor Drives
- Resonant Converters
- Induction Heating
- Multi-level Switch Inverters

The DFM900FXM18-A000 is a dual 1800 volt, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation making the device suitable for the latest drive designs employing pwm and high frequency switching.

These modules incorporate electrically isolated base plates and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DFM900FXM18-A000

Note: When ordering, please use the complete part number.

KEY PARAMETERS

V_{RRM}		1800V
V_F	(typ)	2.0V
I_F	(max)	900A
I_{FM}	(max)	1800A

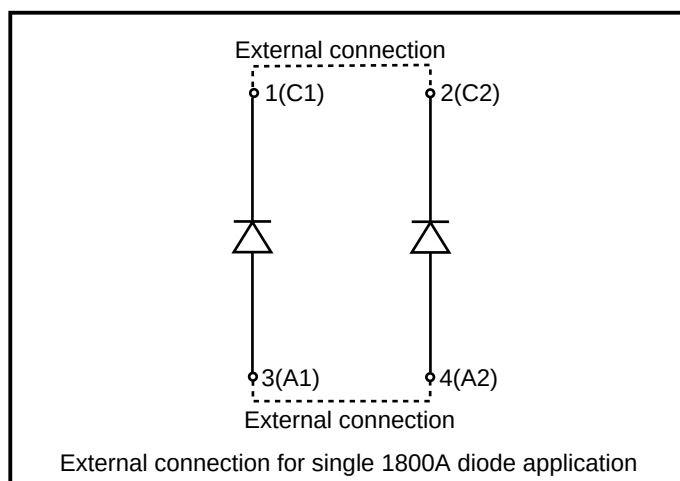


Fig. 1 Circuit diagram

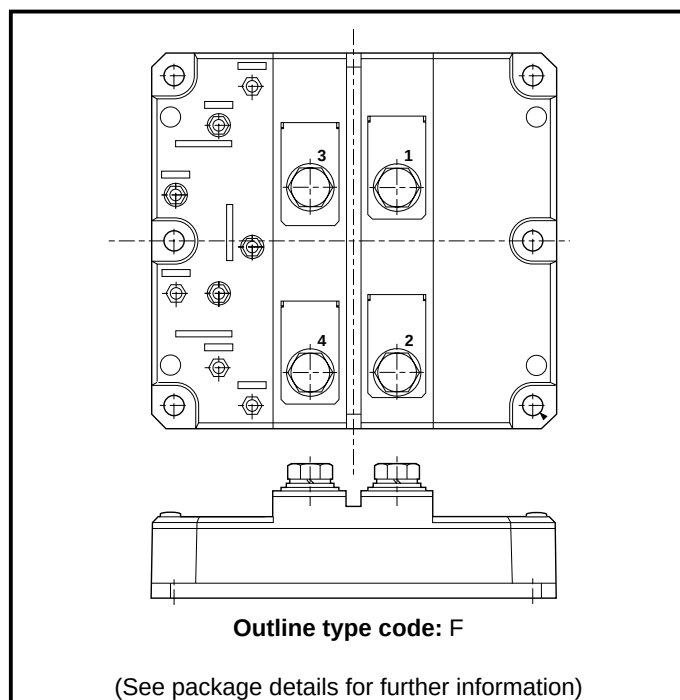


Fig. 2 Electrical connections - (not to scale)

ABSOLUTE MAXIMUM RATINGS - PER ARM

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{RRM}	Repetitive peak reverse voltage	$T_{vj} = 125^{\circ}\text{C}$	1800	V
I_F	Forward current (per arm)	DC, $T_{case} = 75^{\circ}\text{C}$, $T_{vj} = 125^{\circ}\text{C}$	900	A
I_{FM}	Max. forward current	$T_{case} = 110^{\circ}\text{C}$, $t_p = 1\text{ms}$	1800	A
I^2t	I^2t value fuse current rating	$V_R = 0$, $t_p = 10\text{ms}$, $T_{vj} = 125^{\circ}\text{C}$	270	kA^2s
P_{max}	Maximum power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_{vj} = 125^{\circ}\text{C}$	3700	W
V_{isol}	Isolation voltage	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4	kV
Q_{pd}	Partial discharge	IEC1287. $V_1 = 1500\text{V}$, $V_2 = 1100\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation: AlN
 Baseplate material: AlSiC
 Creepage distance: 20mm
 Clearance: 10mm
 CTI (Critical Tracking Index): 175

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - diode (per arm)	Continuous dissipation - junction to case	-	-	27	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance - case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	-	-	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
-	Screw torque	Mounting - M6	-	-	5	Nm
		Electrical connections - M8	-	-	10	Nm

STATIC ELECTRICAL CHARACTERISTICS - PER ARM

$T_{vj} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{RM}	Peak reverse current	$V_R = 1800\text{V}$, $T_{vj} = 125^{\circ}\text{C}$	-	-	15	mA
V_F	Forward voltage	$I_F = 900\text{A}$	-	2.0	2.3	V
		$I_F = 900\text{A}$, $T_{vj} = 125^{\circ}\text{C}$	-	2.0	2.3	V
L	Inductance	-	-	20	-	nH

STATIC ELECTRICAL CHARACTERISTICS

$T_{vj} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
L_M	Module inductance (externally connected in parallel)	-	-	15	-	nH

DYNAMIC ELECTRICAL CHARACTERISTICS - PER ARM

$T_{vj} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{rr}	Peak reverse recovery current	$I_F = 900\text{A}$, $di_F/dt = 6000\text{A}/\mu\text{s}$, $V_R = 900\text{V}$	-	660	-	A
Q_{rr}	Reverse recovery charge		-	240	-	μC
E_{rec}	Reverse recovery energy		-	180	-	mJ

$T_{vj} = 125^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{rr}	Peak reverse recovery current	$I_F = 900\text{A}$, $di_F/dt = 6000\text{A}/\mu\text{s}$, $V_R = 900\text{V}$	-	765	-	A
Q_{rr}	Reverse recovery charge		-	410	-	μC
E_{rec}	Reverse recovery energy		-	270	-	mJ

TYPICAL CHARACTERISTICS

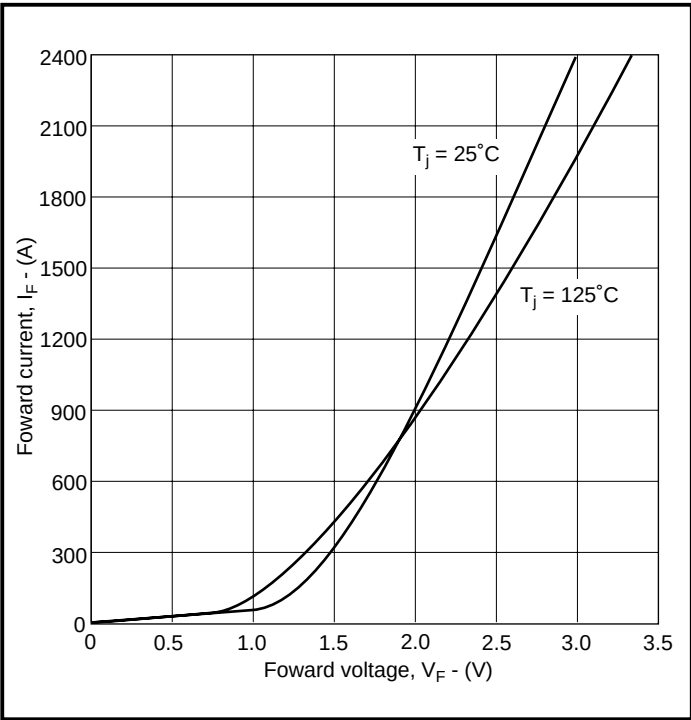


Fig. 2 Diode typical forward characteristics

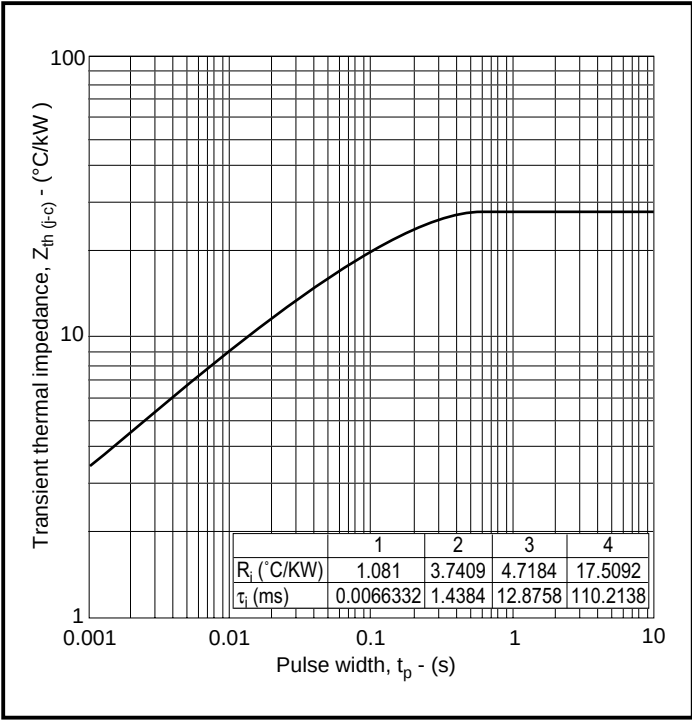


Fig. 4 Transient thermal impedance

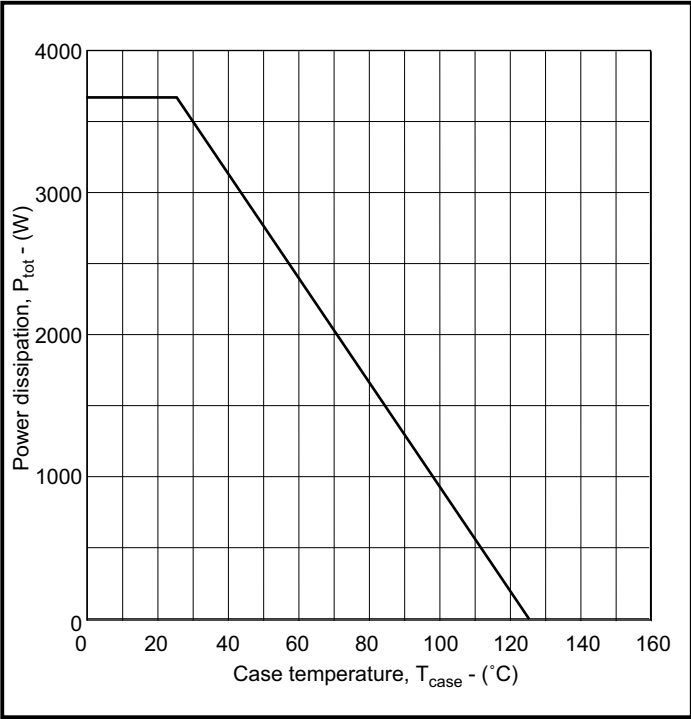


Fig. 5 Power dissipation

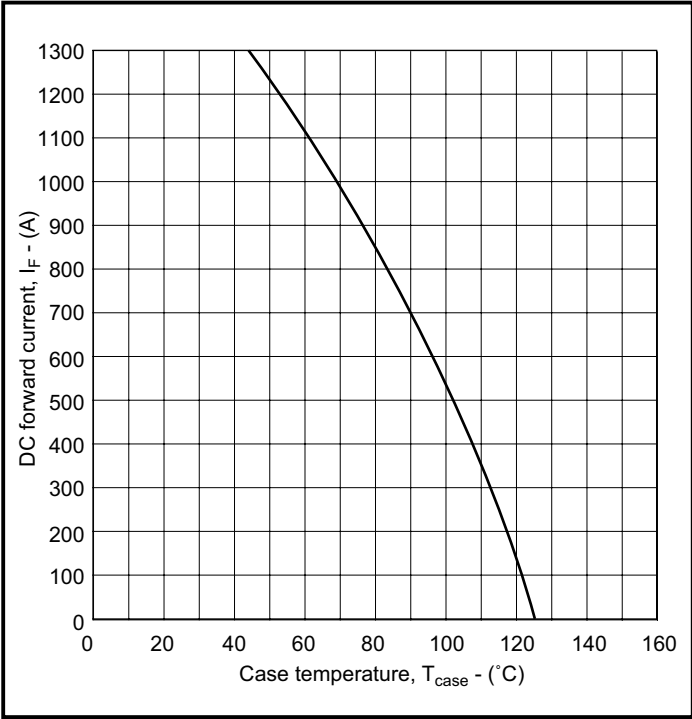


Fig. 6 DC current rating vs case temperature

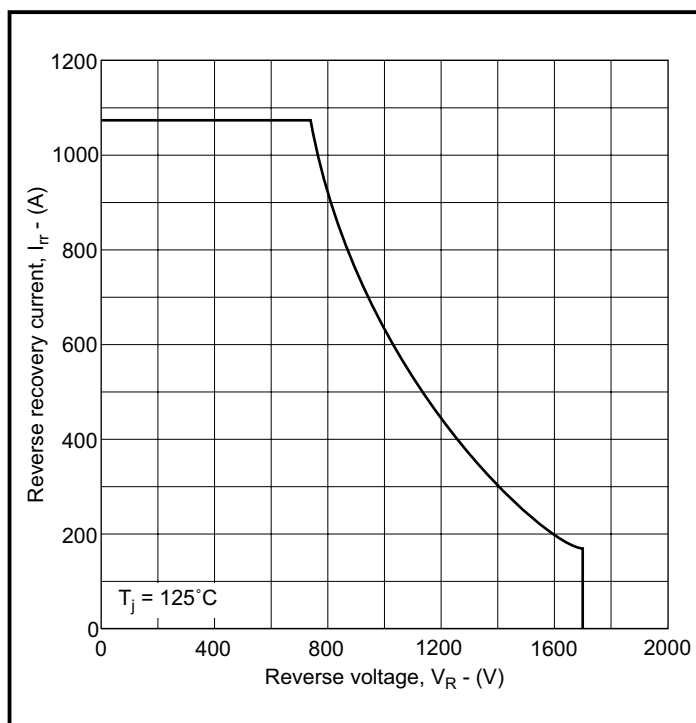
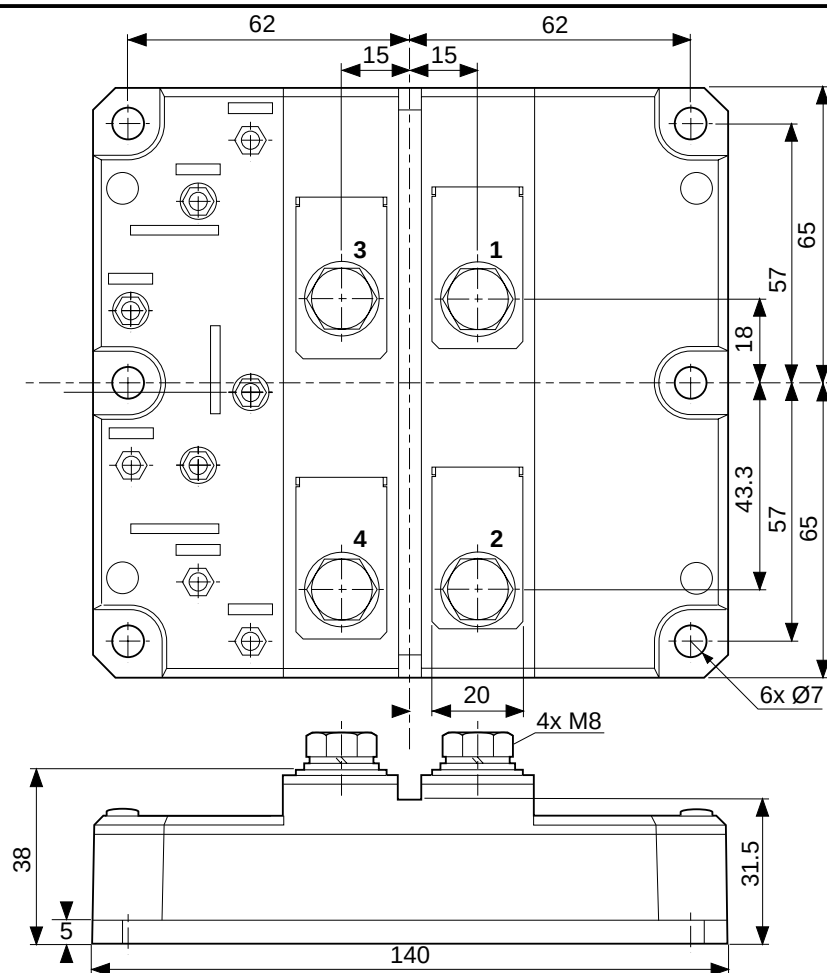


Fig. 7 RBSOA

PACKAGE DETAILS

For further package information, please Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Main Terminal screw plastic hole depth (M8) = 16.8 ± 0.3

Copper terminal thickness, main terminal pins = 1.5 ± 0.1

Nominal weight: 1050g

Module outline type code: F

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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